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1. (Currently Amended) An integrated circuit structure comprising:
first-type transistors and second-type transistors formed on the ~~a~~ same substrate,
wherein said first-type transistors and said second-type transistors comprise:
gate conductors over channel regions in said substrate;
sidewall spacers adjacent said gate conductors; ~~and~~
source and drain extensions on opposite sides of said channel regions, wherein
said sidewall spacers are larger in said first-type transistors than in said second-type transistors;
and
silicide regions between portions of said sidewall spacers and said substrate,
wherein said silicide regions are larger in said first-type transistors than in said second-type
transistors.
2. (Original) The integrated circuit structure in claim 1, wherein said source and drain
extensions are spaced further from said channel regions in said first-type transistors than in said
second-type transistors.
3. (Canceled).
4. (Original) The integrated circuit structure in claim 1, wherein said sidewall spacers
include oxide liners, and
wherein said oxide liners are thicker in said first-type transistors than in said second-type
transistors.
5. (Original) The integrated circuit structure in claim 1, wherein said sidewall spacers
comprise multiple-layer sidewall spacers, and
wherein said sidewall spacers in said first-type transistors have more sidewall spacer
layers than in said second-type transistors.

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6. (Original) The integrated circuit structure in claim 1, wherein said first-type transistors have different performance characteristics than said second-type transistors.
7. (Original) The integrated circuit structure in claim 1, wherein source and drain extensions in said first-type transistors are made of a different material than in said second-type transistors.
8. (Currently Amended) An integrated circuit structure comprising:
P-type field effect transistors (PFETs) and N-type field effect transistors (NFETs)
transistors formed on the a same substrate,
wherein said PFETs and said NFETs comprise:
gate conductors over channel regions in said substrate;
sidewall spacers adjacent said gate conductors; ~~and~~
source and drain extensions on opposite sides of said channel regions, wherein
said sidewall spacers are larger in said PFETs than in said NFETs; and
silicide regions between portions of said sidewall spacers and said substrate,
wherein said silicide regions are larger in said PFETs than in said NFETs.
9. (Original) The integrated circuit structure in claim 8, wherein said source and drain extensions are spaced further from said channel regions in said PFETs than in said NFETs.
10. (Canceled).
11. (Original) The integrated circuit structure in claim 8, wherein said sidewall spacers include oxide liners, and
wherein said oxide liners are thicker in said PFETs than in said NFETs.

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12. (Original) The integrated circuit structure in claim 8, wherein said sidewall spacers comprise multiple-layer sidewall spacers, and
wherein said sidewall spacers in said PFETs have more sidewall spacer layers than in said NFETs.

13. (Original) The integrated circuit structure in claim 8, wherein said PFETs have different performance characteristics than said NFETs.

14. (Original) The integrated circuit structure in claim 8, wherein source and drain extensions in said PFETs are made of a different material than in said NFETs.

15-28 (Canceled).

29. (New) An integrated circuit structure comprising:
first-type transistors and second-type transistors formed on a same substrate,
wherein said first-type transistors and said second-type transistors comprise:
gate conductors over channel regions in said substrate;
sidewall spacers adjacent said gate conductors;
source and drain extensions on opposite sides of said channel regions, and
silicide regions between portions of said sidewall spacers and said substrate,
wherein said silicide regions are larger in said first-type transistors than in said second-type transistors,
wherein said sidewall spacers include oxide liners, and
wherein a size of said silicide regions is modulated by a thickness of said oxide liners.

30. (New) The integrated circuit structure in claim 29, wherein said source and drain extensions are spaced further from said channel regions in said first-type transistors than in said second-type transistors.

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31. (New) The integrated circuit structure in claim 29, wherein said sidewall spacers comprise multiple-layer sidewall spacers, and wherein said sidewall spacers in said first-type transistors have more sidewall spacer layers than in said second-type transistors.
32. (New) The integrated circuit structure in claim 29, wherein said first-type transistors have different performance characteristics than said second-type transistors.
33. (New) The integrated circuit structure in claim 29, wherein source and drain extensions in said first-type transistors are made of a different material than in said second-type transistors.